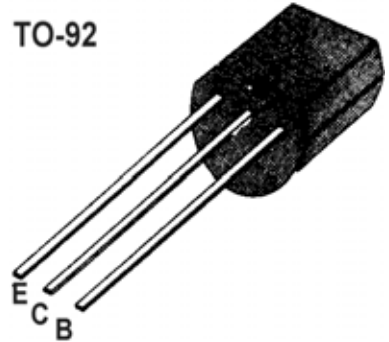


■■ APPLICATION: GENERAL PURPOSE APPLICATION.
■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-35	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-500	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

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■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE}	70		240		V _{CE} = -1V, I _C = -100mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -35V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-35			V	I _C = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-30			V	I _C = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E =-0.1 mA, I _C =0
Base-Emitter Voltage	V _{BE}		-0.8	-1	V	V _{CE} = -1V, I _C = -100mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.1	-0.25	V	I _C = -100mA, I _B = -10mA
Gain bandwidth product	f _T		200		MHz	I _C = -20mA, V _{CE} = -6V
Common Base Output Capacitance	C _{ob}		13		PF	V _{CB} = -6V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification	O	Y
h _{FE}	70~140	120~240